

L Number	Hits	Search Text	DB	Time stamp
1	6802	257/173,328,355-363,546,758.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 18:20
2	1004	438/212,268,309.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 18:21
3	7713	257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 18:21
4	4176	(257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and (semiconductor near (layer substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:13
5	2887	((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and (semiconductor near (layer substrate))) and (source drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:14
6	2154	((((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and (semiconductor near (layer substrate)))) and (source drain)) and (gate near (insulat\$3 oxide electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:14
7	727	(((((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and (semiconductor near (layer substrate)))) and (source drain)) and (gate near (insulat\$3 oxide electrode))) and (interlevel\$1 interconnect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:09
8	143	((((((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and (semiconductor near (layer substrate)))) and (source drain)) and (gate near (insulat\$3 oxide electrode))) and (interlevel\$1 interconnect\$3)) and electrostatic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:10
9	3	("5086365" "5963409" "6080612").PN.	USPAT	2004/04/16 18:54
10	9	("4997786" "5534459" "5610790" "5880001" "5897939" "5899714" "5930638" "5953600" "5970333").PN.	USPAT	2004/04/16 18:54
11	11	("4609931" "4616243" "4692834" "4745450" "5124578" "5272586" "5287241" "5440162" "5479039" "5498892" "5663678").PN.	USPAT	2004/04/16 18:56
12	727	((((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and (semiconductor near (layer substrate)))) and (source drain)) and (gate near (insulat\$3 oxide electrode))) and (interlevel\$1 interconnect\$3 IDL)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:11
13	143	((((((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and (semiconductor near (layer substrate)))) and (source drain)) and (gate near (insulat\$3 oxide electrode))) and (interlevel\$1 interconnect\$3 IDL)) and electrostatic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:11
14	739	(((((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and (semiconductor near (layer substrate)))) and (source drain)) and (gate near (insulat\$3 oxide electrode))) and (interlevel\$1 interconnect\$3 ILD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:14

15	146	(((((257/173,328,355-363,546,758.ccls. or 438/212,268,309.ccls.) and (semiconductor near (layer substrate))) and (source drain)) and (gate near (insulat\$3 oxide electrode))) and (interlevel\$1 interconnect\$3 ILD)) and electrostatic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:13
16	341067	257/\$.ccls. 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:13
17	10480	(257/\$.ccls. 438/\$.ccls.) and electrostatic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:20
18	8796	((257/\$.ccls. 438/\$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:20
19	6392	((257/\$.ccls. 438/\$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)) and (source drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:20
20	3295	(((((257/\$.ccls. 438/\$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat\$3 oxide electrode)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:21
21	1091	(((((257/\$.ccls. 438/\$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat\$3 oxide electrode))) and (interlevel\$1 interconnect\$3 ILD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:18
22	3	(((((257/\$.ccls. 438/\$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat\$3 oxide electrode))) and (interlevel\$1 interconnect\$3 ILD)) and ((first near (interlevel ILD)) with (second near (interlevel ILD)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:19
23	1098	(((((257/\$.ccls. 438/\$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat\$3 oxide electrode))) and (inter\$1level\$1 interconnect\$3 ILD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:21
24	3	(((((257/\$.ccls. 438/\$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat\$3 oxide electrode))) and (inter\$1level\$1 interconnect\$3 ILD)) and ((first near (interlevel ILD)) with (second near (interlevel ILD)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:19
25	3	(((((257/\$.ccls. 438/\$.ccls.) and electrostatic) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat\$3 oxide electrode))) and (inter\$1level\$1 interconnect\$3 ILD)) and ((first near (inter\$1level ILD)) with (second near (inter\$1level ILD)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:22
26	267605	electrostatic ESD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:20

27	71784	((electrostatic ESD) and ((semiconductor near (layer substrate)) substrate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:39
28	39347	((electrostatic ESD) and ((semiconductor near (layer substrate)) substrate)) and (source drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:39
29	5862	((electrostatic ESD) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat\$3 oxide electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:39
30	1783	((electrostatic ESD) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat\$3 oxide electrode))) and (inter\$1level\$1 interconnect\$3 ILD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:28
31	4	((electrostatic ESD) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat\$3 oxide electrode))) and (inter\$1level\$1 interconnect\$3 ILD)) and ((first near (inter\$1level ILD)) with (second near (inter\$1level ILD)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:22
32	11	((electrostatic ESD) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat\$3 oxide electrode))) and (inter\$1level\$1 interconnect\$3 ILD)) and ((first near (inter\$1level ILD)) same (second near (inter\$1level ILD)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:24
33	0	(first near gate near interconnect\$3) with (first near drain near interconnect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:36
34	0	(first near gate near interconnect\$3) same (first near drain near interconnect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:26
35	2	(first near gate near interconnect\$3) and (first near drain near interconnect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:26
36	253785	((semiconductor near (layer substrate)) substrate) same (source drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:27
37	31265	((semiconductor near (layer substrate)) substrate) same (source drain)) and ((gate near (insulat\$3 oxide)) with (gate near electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:28
38	5854	((semiconductor near (layer substrate)) substrate) same (source drain)) and ((gate near (insulat\$3 oxide)) with (gate near electrode))) and (inter\$1level\$1 interconnect\$3 ILD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:39

39	186	(gate near interconnect\$3) with (drain near interconnect\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:29
40	46	(((((semiconductor near (layer substrate)) substrate) same (source drain)) and ((gate near (insulat\$3 oxide)) with (gate near electrode))) and (inter\$1level\$1 interconnect\$3 ILD)) and ((gate near interconnect\$3) with (drain near interconnect\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:29
41	0	(first near gate near (contact\$3 interconnect\$3)) with (first near drain near (contact3 interconnect\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:37
42	197	(gate near (contact\$3 interconnect\$3)) with (drain near (contact3 interconnect\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:37
43	23	((gate near (contact\$3 interconnect\$3)) with (drain near (contact3 interconnect\$3))) and (electrostatic ESD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:49
44	158	((gate near (contact\$3 interconnect\$3)) with (drain near (contact3 interconnect\$3))) and ((semiconductor near (layer substrate)) substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:48
45	158	((gate near (contact\$3 interconnect\$3)) with (drain near (contact3 interconnect\$3))) and ((semiconductor near (layer substrate)) substrate)) and (source drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:48
46	141	((gate near (contact\$3 interconnect\$3)) with (drain near (contact3 interconnect\$3))) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat\$3 oxide electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:48
47	141	((gate near (contact\$3 interconnect\$3)) with (drain near (contact3 interconnect\$3))) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat\$3 oxide electrode))) and (inter\$1level\$1 interconnect\$3 ILD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:47
48	398	(first near (inter\$1level ILD)) with (second near (inter\$1level ILD))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:50
49	374	((first near (inter\$1level ILD)) with (second near (inter\$1level ILD))) and ((semiconductor near (layer substrate)) substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:48
50	274	((first near (inter\$1level ILD)) with (second near (inter\$1level ILD))) and ((semiconductor near (layer substrate)) substrate)) and (source drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:48

L Number	Hits	Search Text	DB	Time stamp
51	222	(((((first near (inter\$1level ILD)) with (second near (inter\$1level ILD))) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat\$3 oxide electrode)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:49
52	4	(((((first near (inter\$1level ILD)) with (second near (inter\$1level ILD))) and ((semiconductor near (layer substrate)) substrate)) and (source drain)) and (gate near (insulat\$3 oxide electrode))) and (electrostatic ESD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:49
53	57	((first near (inter\$1level ILD)) with (second near (inter\$1level ILD)) with (third near (inter\$1level ILD)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 19:57
54	6	((first near (inter\$1level ILD)) with (second near (inter\$1level ILD))) and ((gate near (interconnect contact wir\$3)) with (drain near (interconnect contact wir\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 20:12
55	2004	((gate near (interconnect contact wir\$3)) with (drain near (interconnect contact wir\$3)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 20:13
56	179	((gate near (interconnect contact wir\$3)) with (drain near (interconnect contact wir\$3))) and (electrostatic ESD)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/04/16 20:13